

Silizium-PIN-Fotodiode
Silicon PIN Photodiode
Lead (Pb) Free Product - RoHS Compliant

BPX 61



Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm
- Kurze Schaltzeit (typ. 20 ns)
- Hermetisch dichte Metallbauform (ähnlich TO-5)

Anwendungen

- Lichtschranken für Gleich- und Wechsellichtbetrieb
- IR-Fernsteuerungen
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 400 nm to 1100 nm
- Short switching time (typ. 20 ns)
- Hermetically sealed metal package (similar to TO-5)

Application

- Photointerrupters
- IR-remote controls
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code
BPX 61	Q62702P0025

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 125	°C
Sperrspannung Reverse voltage	V_R	32	V
Verlustleistung, $T_A = 25\text{ °C}$ Total power dissipation	P_{tot}	250	mW

Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$)
Characteristics ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$)

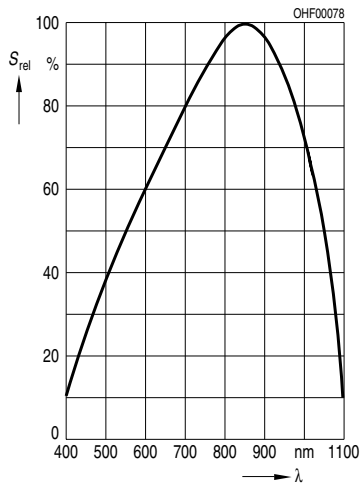
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Fotoempfindlichkeit, $V_R = 5\text{ V}$ Spectral sensitivity	S	70 (≥ 50)	nA/lx
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	850	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{max} Spectral range of sensitivity $S = 10\%$ of S_{max}	λ	400 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	7.00	mm ²
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	2.65×2.65	mm × mm
Halbwinkel Half angle	φ	± 55	Grad deg.
Dunkelstrom, $V_R = 10\text{ V}$ Dark current	I_R	2 (≤ 30)	nA
Spektrale Fotoempfindlichkeit, $\lambda = 850\text{ nm}$ Spectral sensitivity	S_λ	0.62	A/W
Quantenausbeute, $\lambda = 850\text{ nm}$ Quantum yield	η	0.90	<u>Electrons</u> Photon
Leerlaufspannung, $E_v = 1000\text{ lx}$ Open-circuit voltage	V_O	375 (≥ 320)	mV
Kurzschlussstrom, $E_v = 1000\text{ lx}$ Short-circuit current	I_{SC}	70	μA

Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$)

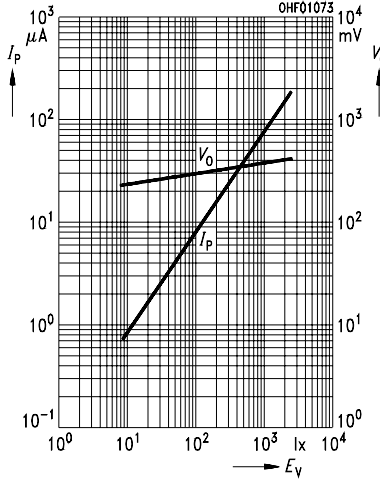
Characteristics ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$) (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Anstiegs- und Abfallzeit des Fotostroms Rise and fall time of the photocurrent $R_L = 50\ \Omega$; $V_R = 5\text{ V}$; $\lambda = 850\text{ nm}$; $I_p = 800\ \mu\text{A}$	t_r, t_f	20	ns
Durchlassspannung, $I_F = 100\text{ mA}$, $E = 0$ Forward voltage	V_F	1.3	V
Kapazität, $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_0	72	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	- 2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC}	TC_I	0.18	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10\text{ V}$, $\lambda = 850\text{ nm}$	NEP	4.1×10^{-14}	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 10\text{ V}$, $\lambda = 850\text{ nm}$ Detection limit	D^*	6.6×10^{12}	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

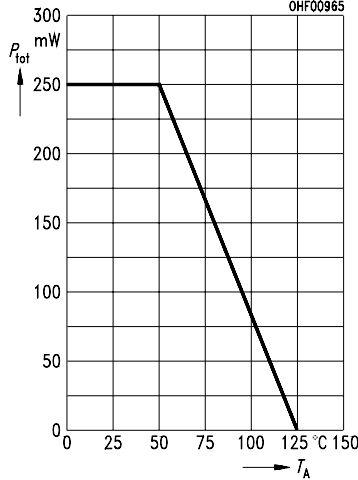
Relative Spectral Sensitivity
 $S_{rel} = f(\lambda)$



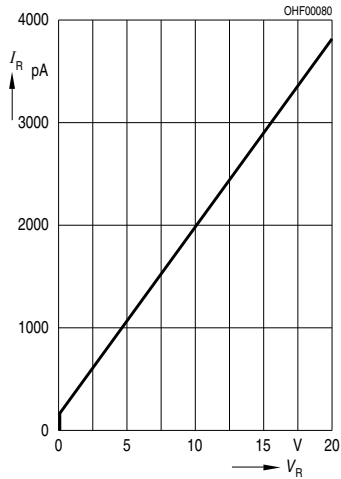
Photocurrent $I_P = f(E_V)$, $V_R = 5\text{ V}$
Open-Circuit Voltage $V_O = f(E_V)$



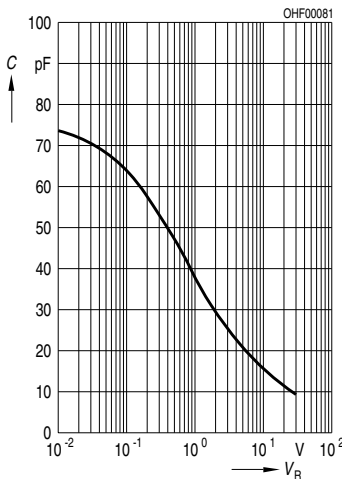
Total Power Dissipation
 $P_{tot} = f(T_A)$



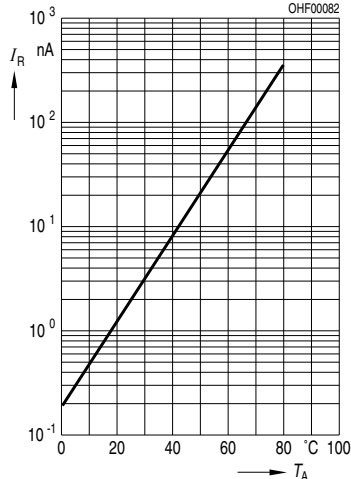
Dark Current
 $I_R = f(V_R), E = 0$



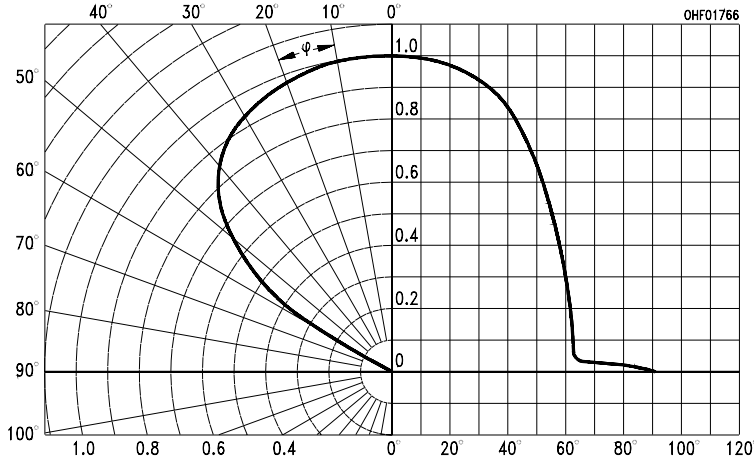
Capacitance
 $C = f(V_R), f = 1\text{ MHz}, E = 0$



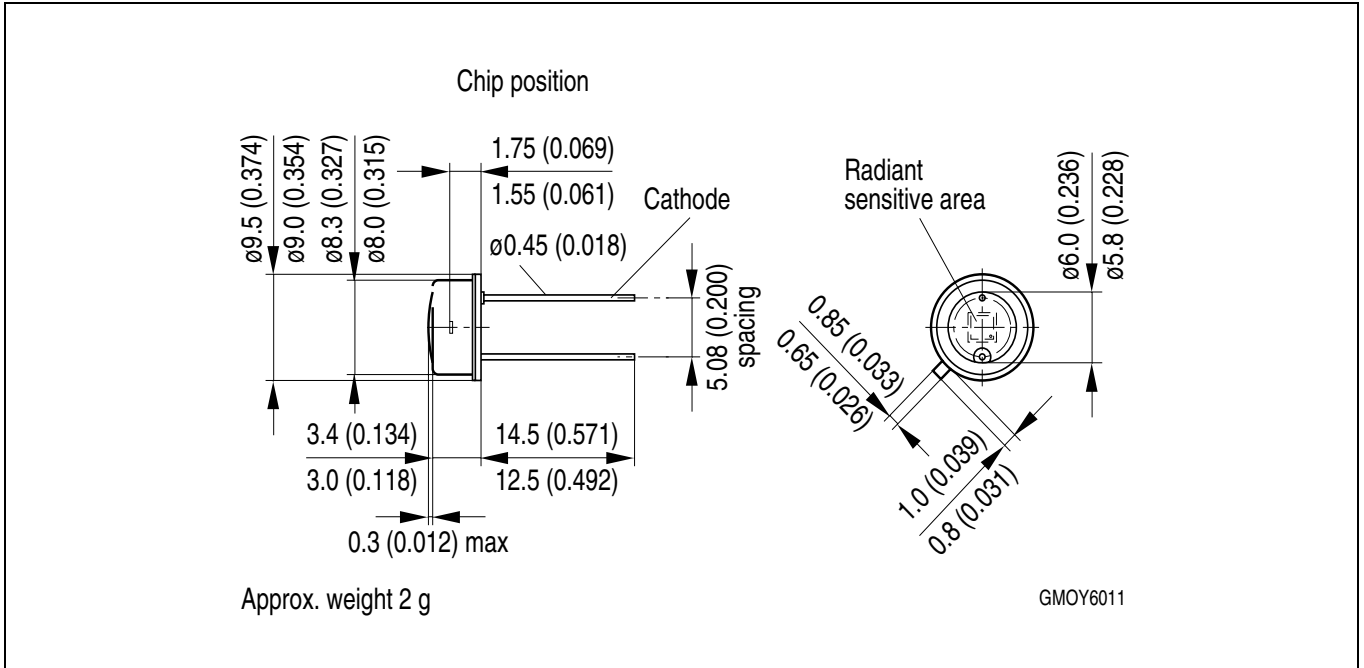
Dark Current
 $I_R = f(T_A), V_R = 5\text{ V}, E = 0$



Directional Characteristics
 $S_{rel} = f(\varphi)$



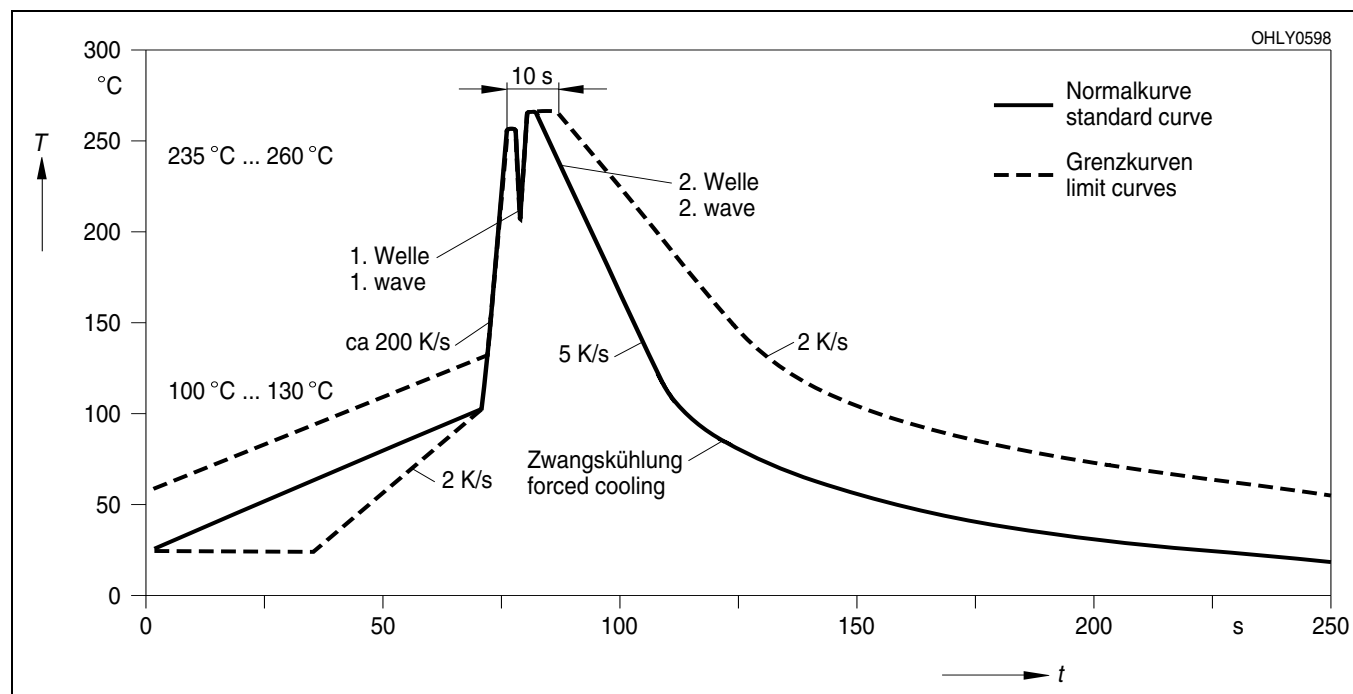
Maßzeichnung
Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
(acc. to CECC 00802)



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² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.